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He received the Ph.D. degree in electronic engineering from Tokyo Institute of Technology. In 2000, he joined the Department of Electronic Engineering at the University of Tokyo. There, he started to study spin-electronic materials and devices. In 2005, he joined the Department of Frontier Informatics at the University of Tokyo, where he studied high performance MOSFETs with high mobility channel. Dr. Sugahara is a member of the Japan Society of Applied Physics.